

ZLM2323AB

V1.0

P-Channel Trench Power MOSFET

ZLW-QW-EN-G146



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Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
-20V	39mΩ@-4.5V	-4.7A
	52mΩ@-2.5V	

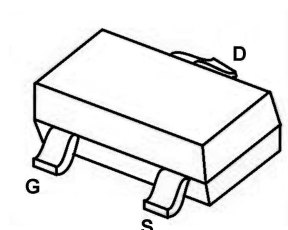
Feature

- TrenchFET Power MOSFET

Application

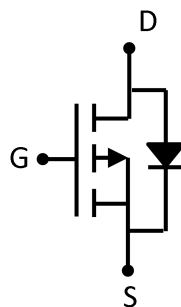
- PA Switch
- Load Switch

Package



SOT-23

Circuit diagram



Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 10	V
Continuous Drain Current	I_D	-4.7	A
Pulsed Drain Current	I_{DM}	-20	A
Power Dissipation	P_D	0.35	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	$^{\circ}\text{C}/\text{W}$
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^{\circ}\text{C}$

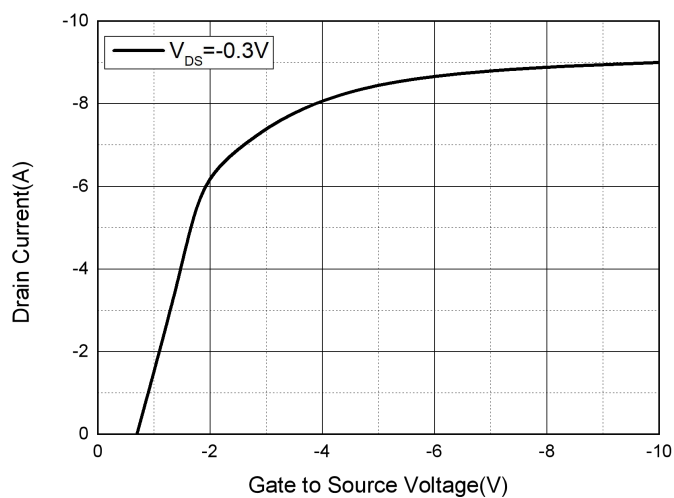
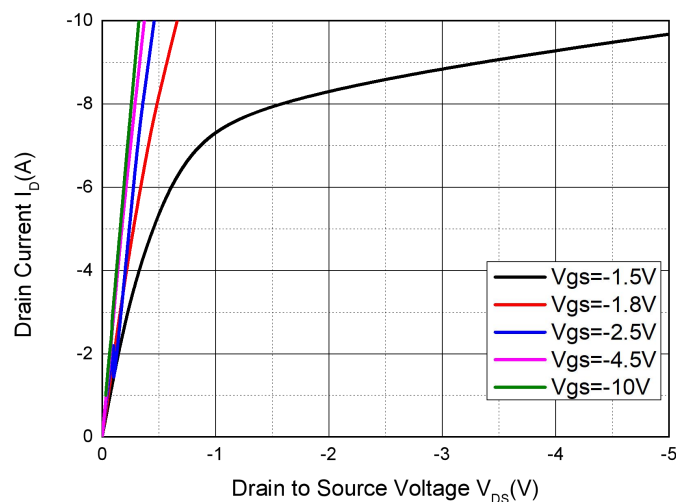
Electrical characteristics (T_A=25 °C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =-250μA	-20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =-16V, V _{GS} = 0V			-1	μA
Gate-body leakage current	I _{GSS}	V _{GS} =±10V, V _{DS} = 0V			±1	μA
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-0.4		-1	V
Drain-source on-resistance	R _{DS(on)}	V _{GS} =-4.5V, I _D =-2.7A		33	39	mΩ
		V _{GS} =-2.5V, I _D =-2.7A		43	52	
Dynamic characteristics						
Input Capacitance ¹⁾²⁾	C _{iss}	V _{DS} =-10V, V _{GS} =0V, f =1MHz		1020		pF
Output Capacitance ¹⁾²⁾	C _{oss}			191		pF
Reverse Transfer Capacitance ¹⁾²⁾	C _{rss}			140		pF
Total Gate Charge ¹⁾	Q _g	V _{DS} =-10V, V _{GS} =-4.5V, I _D =-4.7A		12.5	19	nC
Gate-Source Charge ¹⁾	Q _{gs}			1.7		nC
Gate-Drain Charge ¹⁾	Q _{gd}			3.3		nC
Switching ¹⁾²⁾						
Turn-on delay time	t _{d(on)}	V _{GEN} =-4.5V, V _{DD} =-10V, I _D =-1A, R _G =6Ω		25	40	ns
Turn-on rise time	t _r			43	65	ns
Turn-off delay time	t _{d(off)}			71	110	ns
Turn-off fall time	t _f			48	75	ns
Source-Drain Diode characteristics						
Diode Forward voltage	V _{SD}	V _{GS} =0V, I _S =-1A			-1.2	V

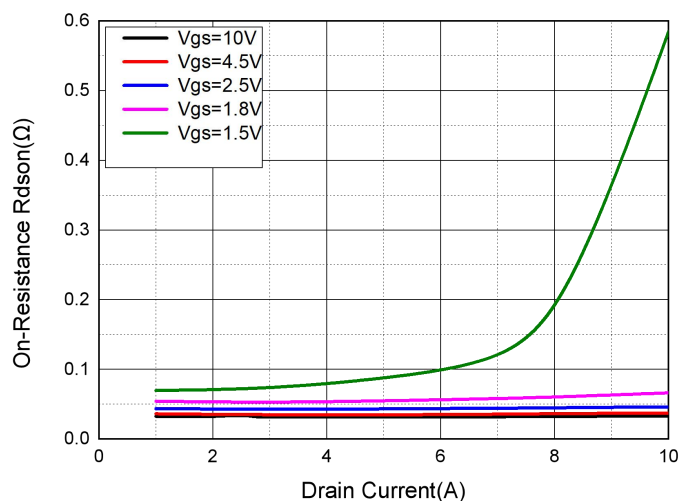
Notes:

- 1) Pulse test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 2) These parameters have no way to verify.

Typical Characteristics

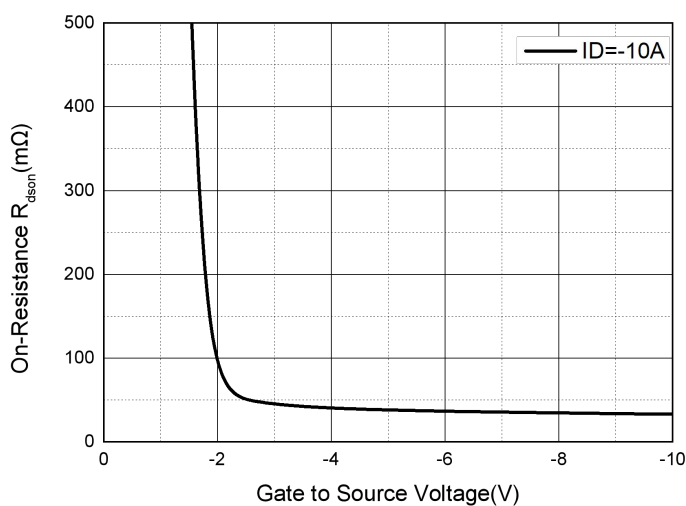


Output Characteristics

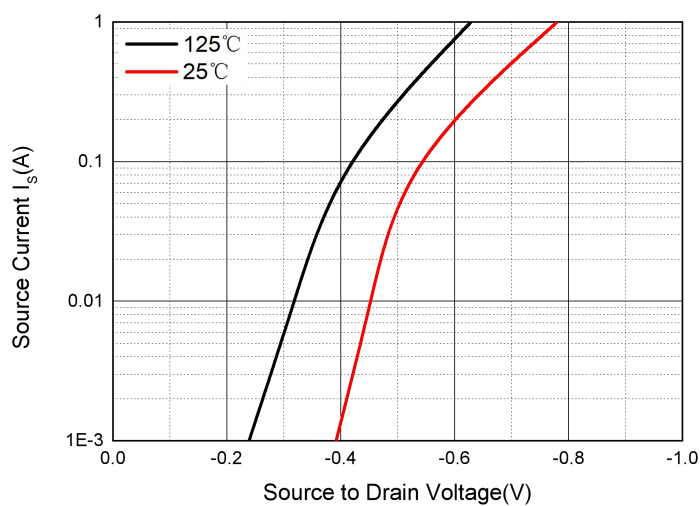


$R_{DS(ON)}$ vs. I_D

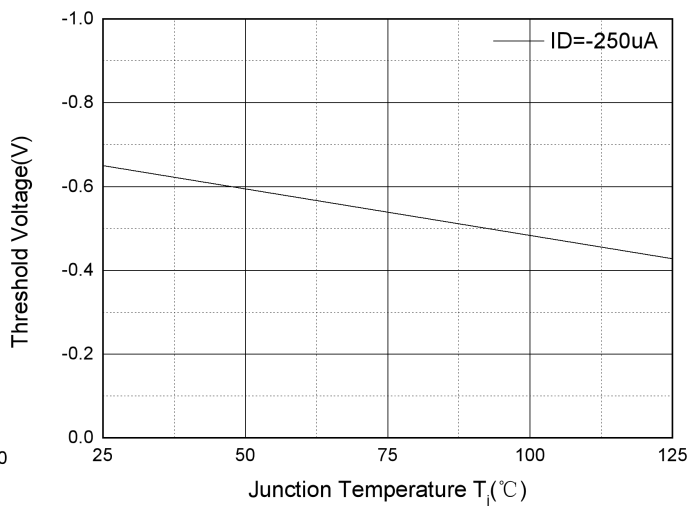
Transfer Characteristics



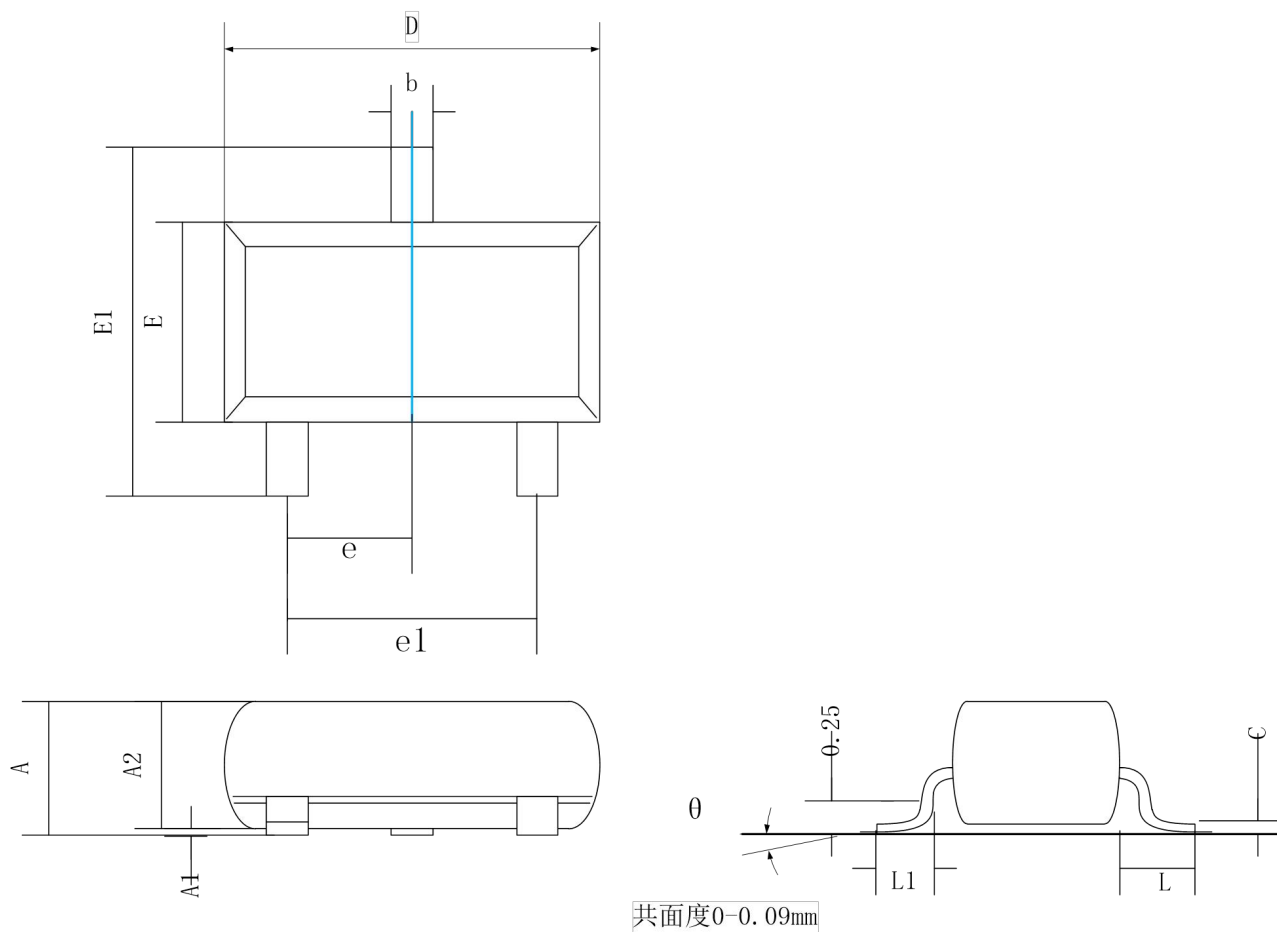
$R_{DS(ON)}$ vs. V_{GS}



I_S vs. V_{SD}



Threshold Voltage

SOT-23 Package Information


Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.90	1.15
A1	0.00	0.10
A2	0.90	1.05
b	0.30	0.50
c	0.08	0.15
D	2.80	3.00
E	1.20	1.40
E1	2.25	2.55
e	0.95 REF.	
e1	1.80	2.00
L	0.55 REF.	
L1	0.30	0.50
θ	0°	8°